

G () G

XTgheXf

CebWhVgFh Td

cc VTgbaf

Uf b hgX Tk h ETga f

CTeT XgXe	6baWgbaf	FI Ub	I T hXf	Ha g
	°C			



G () G

XVge VT 6 TeTVgXef g Vf

CTeT XgXe	6 baWgbaf	FI Ub	I T hXf			Ha g
			a	Gl c	Tk	
	°C					
	°C					

Bezeichnung

Typ	Teilenummer	CTV T X	J X g	aaXe5bk	CXe6 Tgba

Geometrische Abmessungen

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

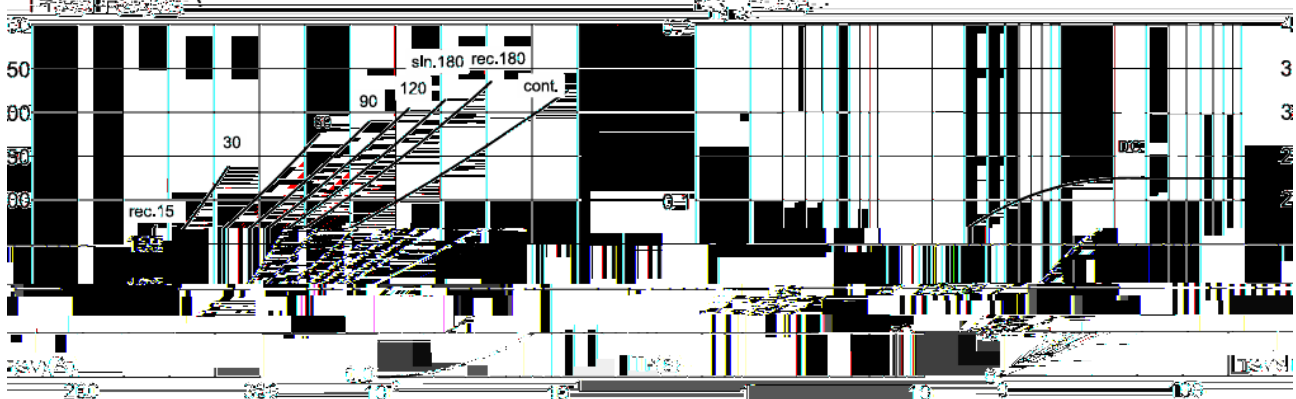


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

FIG.3: Forward characteristics (per thyristor or diode)

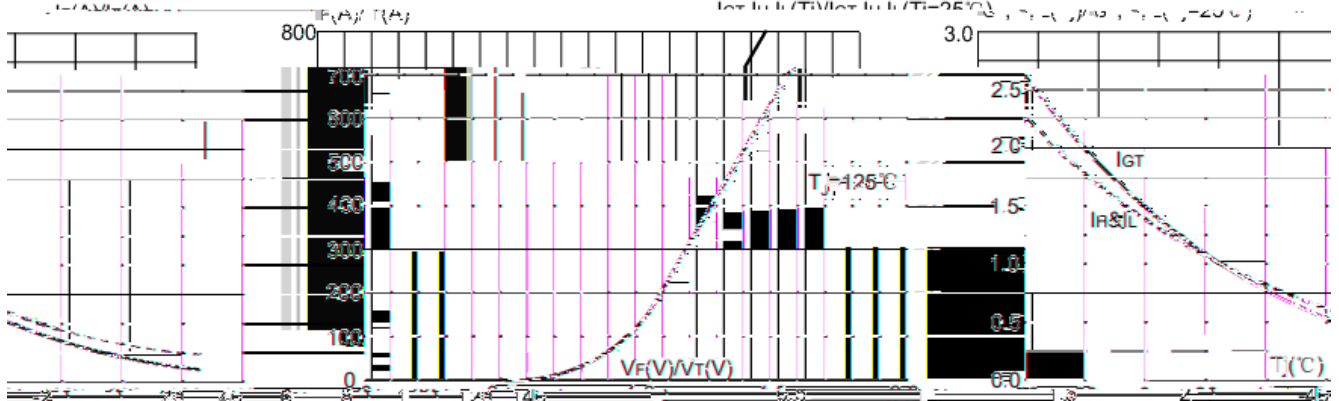


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

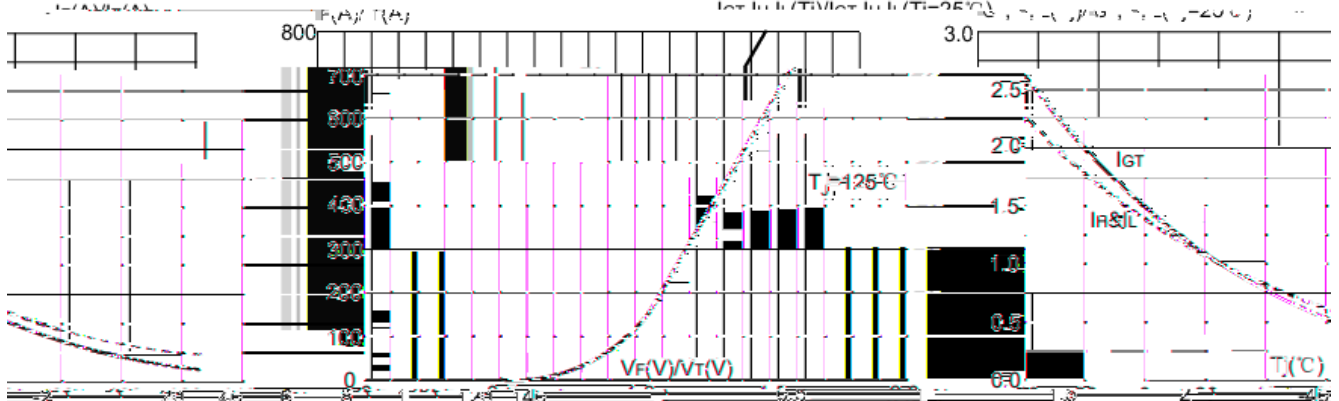


FIG.5: Gate trigger current vs. junction temperature

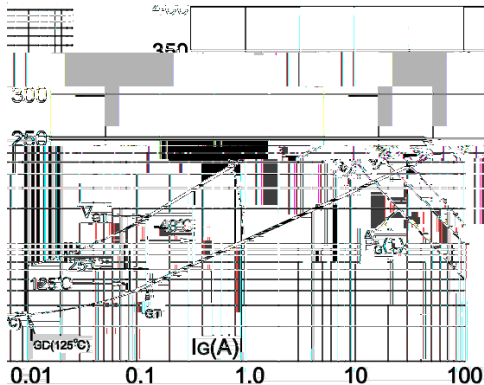
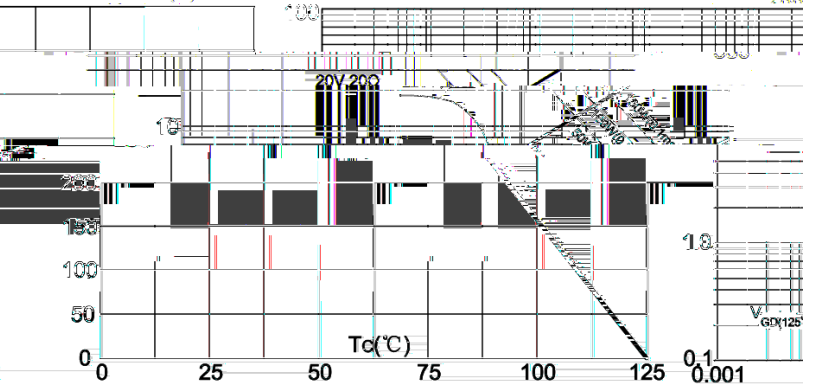
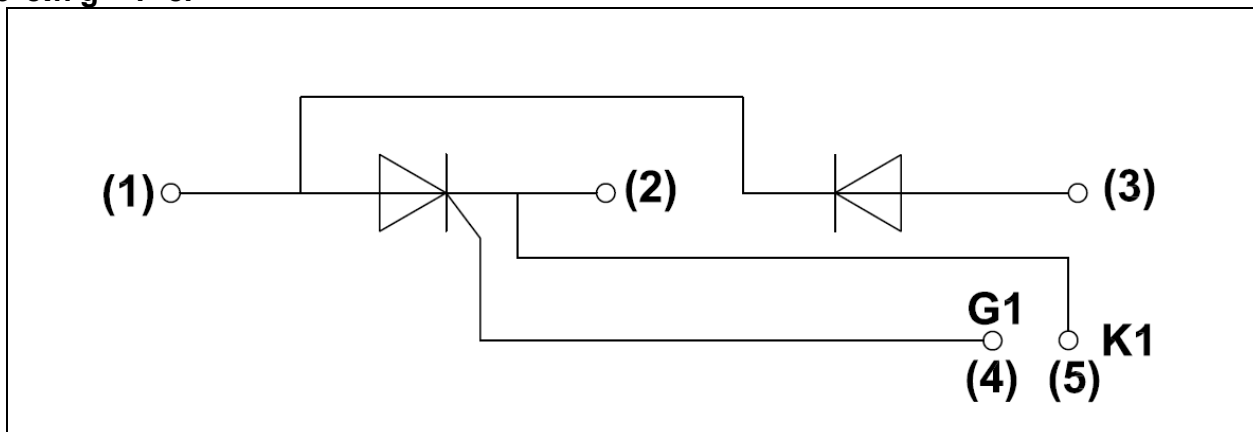


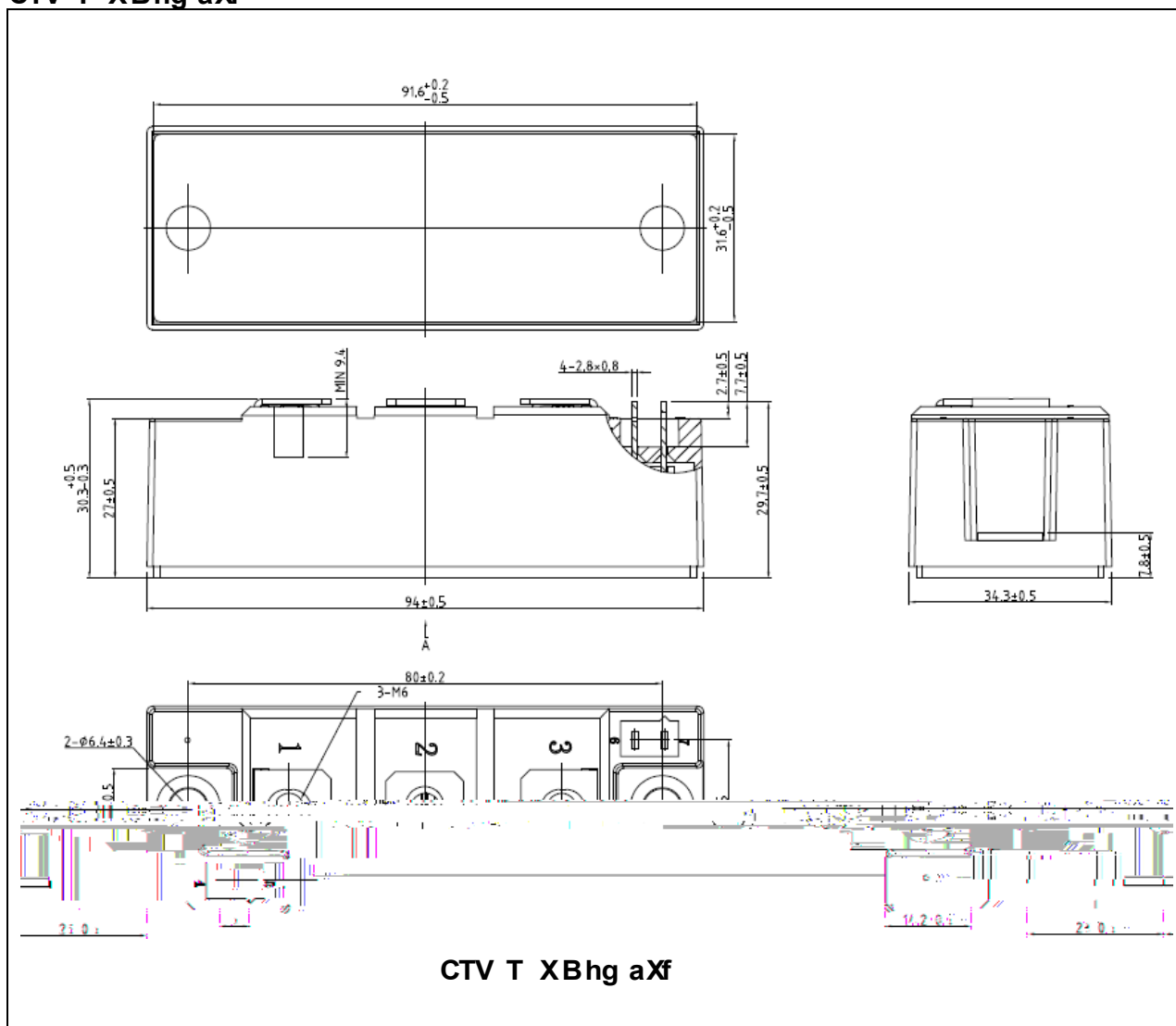
FIG.6: Forward current vs. temperature



6 eVh g T eT



CTV T XBhg aXf





G () G

